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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.4V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pjgfb-x0

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Table 1-1.	List of Ordering Part Numbers
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				(4/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
44 pins	44-pin plastic LQFP	Mounted	А	R5F100FAAFP#V0, R5F100FCAFP#V0, R5F100FDAFP#V0,
	(10 $ imes$ 10 mm, 0.8 mm			R5F100FEAFP#V0, R5F100FFAFP#V0, R5F100FGAFP#V0,
	pitch)			R5F100FHAFP#V0, R5F100FJAFP#V0, R5F100FKAFP#V0,
				R5F100FLAFP#V0
				R5F100FAAFP#X0, R5F100FCAFP#X0, R5F100FDAFP#X0,
				R5F100FEAFP#X0, R5F100FFAFP#X0, R5F100FGAFP#X0,
				R5F100FHAFP#X0, R5F100FJAFP#X0, R5F100FKAFP#X0,
				R5F100FLAFP#X0
			D	R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0,
				R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0,
				R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0,
				R5F100FLDFP#V0
				R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0,
				R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0,
				R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0,
				R5F100FLDFP#X0
			G	R5F100FAGFP#V0, R5F100FCGFP#V0, R5F100FDGFP#V0,
				R5F100FEGFP#V0, R5F100FFGFP#V0, R5F100FGGFP#V0,
				R5F100FHGFP#V0, R5F100FJGFP#V0
				R5F100FAGFP#X0, R5F100FCGFP#X0, R5F100FDGFP#X0,
				R5F100FEGFP#X0, R5F100FFGFP#X0, R5F100FGGFP#X0,
				R5F100FHGFP#X0, R5F100FJGFP#X0
		Not	А	R5F101FAAFP#V0, R5F101FCAFP#V0, R5F101FDAFP#V0,
		mounted		R5F101FEAFP#V0, R5F101FFAFP#V0, R5F101FGAFP#V0,
				R5F101FHAFP#V0, R5F101FJAFP#V0, R5F101FKAFP#V0,
				R5F101FLAFP#V0
				R5F101FAAFP#X0, R5F101FCAFP#X0, R5F101FDAFP#X0,
				R5F101FEAFP#X0, R5F101FFAFP#X0, R5F101FGAFP#X0,
				R5F101FHAFP#X0, R5F101FJAFP#X0, R5F101FKAFP#X0,
				R5F101FLAFP#X0
			D	R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0,
				R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0,
				R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0,
				R5F101FLDFP#V0
				R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0,
				R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0,
				R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0,
				R5F101FLDFP#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

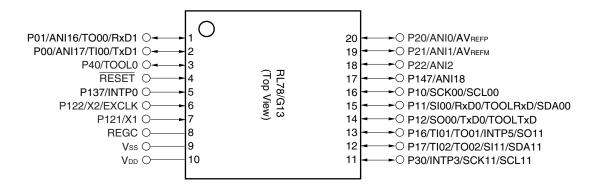
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



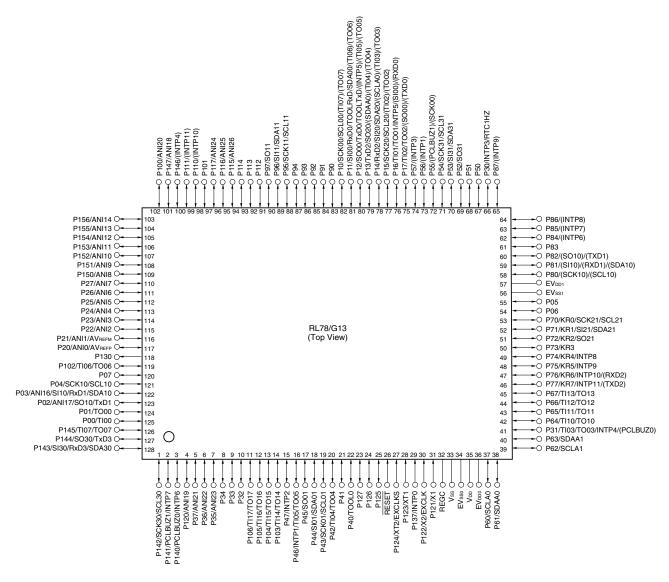
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.



1.3.14 128-pin products

• 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

- 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

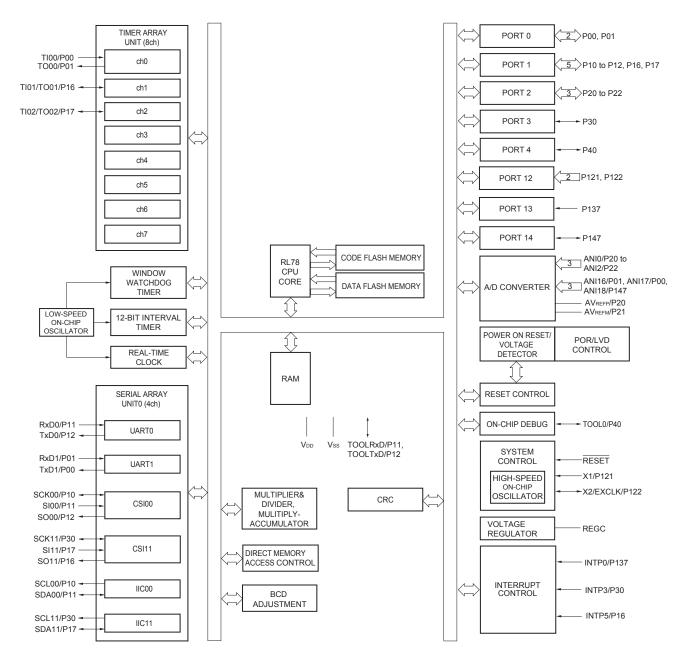
Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.5 Block Diagram

1.5.1 20-pin products





 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

^{3.} When setting to PIOR = 1

Item		40	nin	11	nin	10	nin	EO	nin	(2/2) 64-pin	
Ite		40-			-pin		-pin	52	-pin I		
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	:	2		2		2		2		2
·		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsuB = 32.768 kHz operation) 									
8/10-bit resolution	A/D converter	9 channe	ls	10 chanr	nels	10 chanr	nels	12 chan	nels	12 chanr	nels
Serial interface		[40-pin, 4	4-pin prod	ducts]		J				J	
	 CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [48-pin, 52-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 1 channel/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel 										
	I ² C bus	1 channe		1 channe		1 channe		1 channe		1 channe	
Multiplier and divid		 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 									
		 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 									
DMA controller		2 channe	ls								
Vectored	Internal	2	27	:	27	2	27		27	2	27
interrupt sources	External		7		7		10		12		13
Key interrupt			4		4		6		8		8
Reset	 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access 										
Power-on-reset ci	rcuit		on-reset: down-res	1.51 V et: 1.50 V	. ,						
Voltage detector		Rising edge : 1.67 V to 4.06 V (14 stages) Falling edge : 1.63 V to 3.98 V (14 stages)									
On-chip debug fur	nction	Provided									
Power supply volta				$T_A = -40 \text{ to}$ $T_A = -40 \text{ to}$							
Operating ambien	t temperature	$T_A = 40 to$	o +85°C (/		ner applica	itions, D: Ii ations)	ndustrial a	pplication	s)		

<R>

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins] [5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT	HS (high-	$f_{H} = 32 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 V$		0.62	1.86	mA
current	Note 2	mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.62	1.86	mA
			mode	fiH = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.45	mA
					V _{DD} = 3.0 V		0.50	1.45	mA
				fiH = 16 MHz ^{Note 4}	$V_{DD} = 5.0 V$		0.44	1.11	mA
					$V_{DD} = 3.0 V$		0.44	1.11	
			10//						mA
			LS (low- speed main) mode ^{Note 7}	$f_{IH} = 8 MHz^{Note 4}$	V _{DD} = 3.0 V V _{DD} = 2.0 V		290 290	620 620	μΑ μΑ
		LV (low-	file = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		440	680	μA	
			voltage main) mode		V _{DD} = 2.0 V		440	680	μA
		HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.08	mA	
		speed main) mode ^{Note 7}	$V_{DD} = 5.0 V$	Resonator connection		0.48	1.28	mA	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.08	mA
			$V_{DD} = 3.0 V$	Resonator connection		0.48	1.28	mA	
		$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	0.63	mA		
			$V_{DD} = 5.0 V$	Resonator connection		0.28	0.71	mA	
		f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.21	0.63	mA		
				$V_{DD} = 3.0 \text{ V}$	Resonator connection		0.28	0.71	mA
			LS (low-	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		110	360	μA
		speed	speed main) mode ^{№ote 7}	V _{DD} = 3.0 V	Resonator connection		160	420	μA
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		110	360	μA
				V _{DD} = 2.0 V	Resonator connection		160	420	μA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μA
			clock operation	$T_A = -40^{\circ}C$	Resonator		0.47	0.80	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μA
				$T_A = +25^{\circ}C$	Resonator connection		0.53	0.80	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.60	2.49	μA
				fs∪в = 32.768 kHz ^{№te 5}	Square wave input	1	0.64	4.03	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.83	4.22	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		1.09	8.04	μA
IDD3 ^{Note}				$T_{A} = +85^{\circ}C$	Resonator connection		1.28	8.23	μA
	DD3 ^{Note 6}	STOP	$T_A = -40^{\circ}C$				0.19	0.52	μA
		mode ^{Note 8}	T _A = +25°C			1	0.25	0.52	μΑ
			$T_A = +25 \text{ C}$ $T_A = +50^{\circ}\text{C}$				0.32	2.21	μA
			$T_{A} = +70^{\circ}C$				0.55	3.94	μA
			$T_{A} = +85^{\circ}C$				1.00	7.95	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into Vbb, EVbbb, and EVbb1, including the input leakage current flowing when the level of the input pin is fixed to Vbb, EVbb0, and EVbb1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: ~~ 1.8 V \leq V_{DD} \leq 5.5 V@1 MHz to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	r-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fclk	$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	125		500		1000		ns
			$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	250		500		1000		ns
			$\begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	500		500		1000		ns
			$\begin{array}{l} 1.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	1000		1000		1000		ns
			$\begin{array}{l} 1.6 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	—		1000		1000		ns
SCKp high-/low-level width	tкнı, tкlı	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 12		tксү1/2 – 50		tксү1/2 – 50		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 – 18		tксү1/2 – 50		tксү1/2 – 50		ns
		$2.4~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 – 38		tксү1/2 – 50		tксү1/2 – 50		ns
		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$100 \leq 5.5 \text{ V}$	tксү1/2 – 100		tксү1/2 – 100		tксү1/2 – 100		ns
		$1.6 V \le EV_{DI}$	$500 \leq 5.5 \text{ V}$	—		tксү1/2 – 100		tксү1/2 – 100		ns
SIp setup time	tsik1	$4.0 V \le EV_{DI}$	$100 \leq 5.5 \text{ V}$	44		110		110		ns
(to SCKp↑) Note 1		$2.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$00 \leq 5.5 \text{ V}$	44		110		110		ns
		$2.4 V \le EV_{DI}$	$0.0 \leq 5.5 \text{ V}$	75		110		110		ns
		$1.8 V \le EV_{DI}$	$0.0 \leq 5.5 \text{ V}$	110		110		110		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$0.0 \leq 5.5 \text{ V}$	220		220		220		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V			220		220		ns
SIp hold time	tksi1	$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V	19		19		19		ns
(from SCKp \uparrow) Note 2		$1.6 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V	—		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$\begin{array}{l} 1.7 \ V \leq EV_{DI} \\ C = 30 \ pF^{\text{Note}} \end{array}$			25		25		25	ns
output Note 3		$1.6 V \le EV_{DI}$ C = 30 pF ^{Note}			_		25		25	ns

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_4 = -40$ to $+85^{\circ}$ C, 1.6 V \leq EVppa = EVpp1 \leq Vpp \leq 5.5 V, Vss = EVssa = EVssa = 0 V)

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

Parameter	Symbol	Conditions		h-speed Mode	``	/-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsikı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \end{array}$	81		479		479		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$	177		479		479		ns
		$C_b=30 \text{ pF}, \text{R}_b=2.7 \text{k}\Omega$							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	479		479		479		ns
		C_b = 30 pF, R_b = 5.5 k Ω							
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	19		19		19		ns
		C_b = 30 pF, R_b = 1.4 k Ω							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$	19		19		19		ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	19		19		19		ns
		C_b = 30 pF, R_b = 5.5 k Ω							
Delay time from SCKp↓ to	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_{b} \leq 4.0 \ V, \end{array}$		100		100		100	ns
SOp output Note 1		C_b = 30 pF, R_b = 1.4 k Ω							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \end{array}$		195		195		195	ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$		483		483		483	ns
		C_b = 30 pF, R_b = 5.5 k Ω							

		5 5 V Voo - EVo	$ = EV_{oot} = 0.V$
$T_{A} = -40$ to +85°C,		j.j v, vss = ⊑vs	$s_0 = \Box v s s_1 = U v $

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with $EV_{DD0} \ge V_b$.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

2.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclк	$1.8~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years Ta = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \leq \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~V \leq V_{\text{DD}} < 2.7~V$	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator**.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.0		+1.0	%
		–40 to –20 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	DD2	HALT mode	HS (high- speed main) mode ^{Note 7}	fin = 32 MHz ^{Note 4}	$V_{DD} = 5.0 V$		0.54	2.90	mA
	Note 2				$V_{DD} = 3.0 V$		0.54	2.90	mA
				$f_{IH} = 24 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.44	2.30	mA
					V _{DD} = 3.0 V		0.44	2.30	mA
				$f_{iH} = 16 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 V$		0.40	1.70	mA
					V _{DD} = 3.0 V		0.40	1.70	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{Note 3}$,	Square wave input		0.28	1.90	mA
		speed main) mode ^{Note 7}	$V_{DD} = 5.0 V$	Resonator connection		0.45	2.00	mA	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.90	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.45	2.00	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.26	1.10	mA
			Subsystem clock operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA
				$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μA
				$T_A = +25^{\circ}C$	Resonator connection		0.49	0.76	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.56	1.36	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.72	2.16	μA
			fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μA	
				$T_A = +85^{\circ}C$	Resonator connection		1.01	3.56	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	μA
				$T_A = +105^{\circ}C$	Resonator connection		3.20	15.56	μA
		IDD3 ^{Note 6} STOP mode ^{Note 8}	$T_{\text{A}} = -40^{\circ}\text{C}$				0.18	0.50	μA
			$T_A = +25^{\circ}C$				0.23	0.50	μA
			$T_A = +50^{\circ}C$				0.30	1.10	μA
			$T_A = +70^{\circ}C$			0.46	1.90	μA	
			T _A = +85°C	$T_{A} = +85^{\circ}C$ $T_{A} = +105^{\circ}C$			0.75	3.30	μA
			T _A = +105°C				2.94	15.30	μA

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq EV_{DD0} \leq V_{DD} \leq 5.5$ V, Vss = EVss₀ = 0 V) (2/2)

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz

2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- **Remarks 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



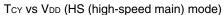
- **Notes 1.** Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVSSD, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

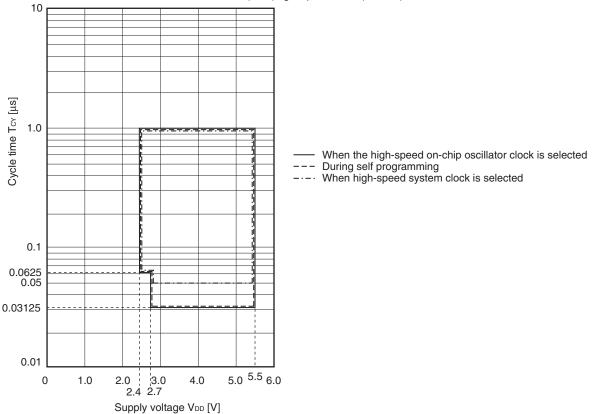
HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V_DD \leq 5.5 V@1 MHz to 16 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. file: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

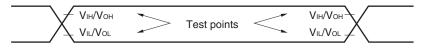


Minimum Instruction Execution Time during Main System Clock Operation

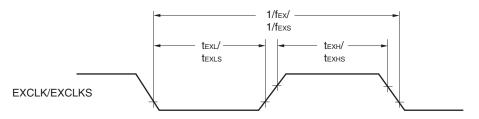




AC Timing Test Points

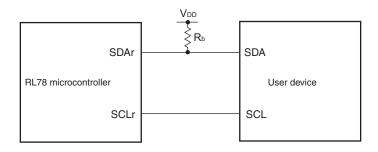


External System Clock Timing

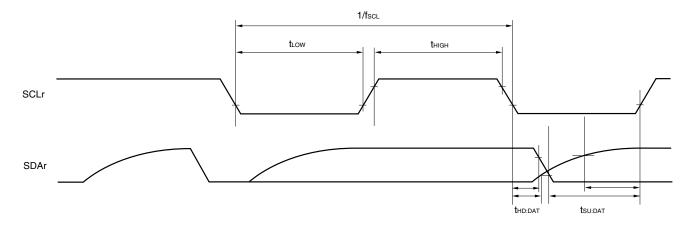




Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
 h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

= 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



5. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

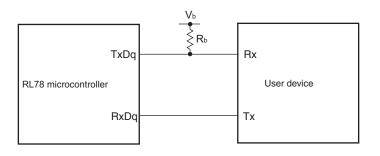
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$

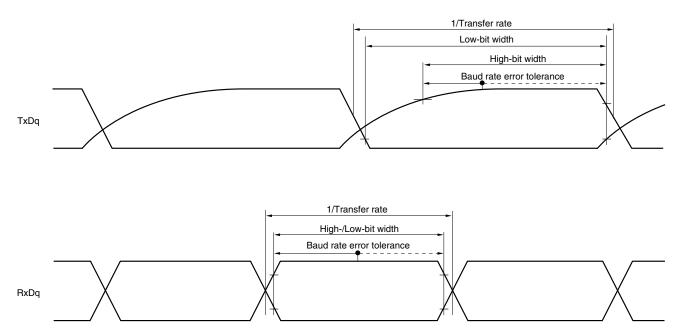
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)







UART mode bit width (during communication at different potential) (reference)

 Remarks 1.
 Rb[Ω]:Communication line (TxDq) pull-up resistance,

 Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

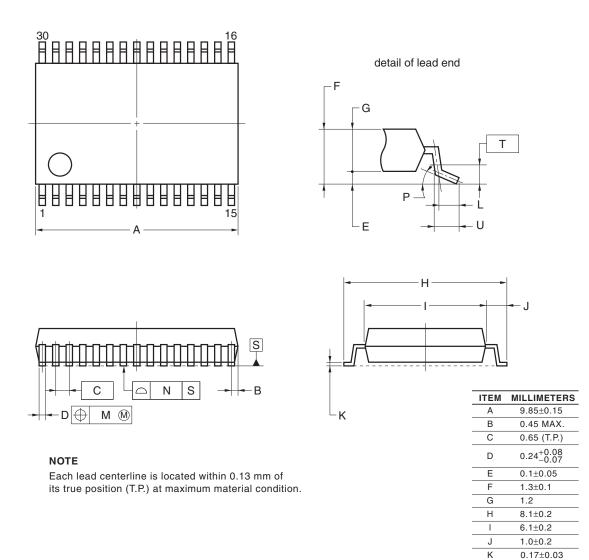
4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18





0.5

0.13

0.10 3°+5°

0.25

0.6±0.15

L

M N

P T

U

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